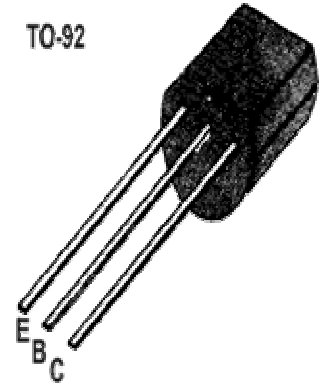


■ ■ APPLICATION: POWER AMPLIFIER APPLICATION,

SWITCHING APPLICATION.

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-200	mA
Collector Power Dissipation	P _C	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	80		300		V _{CE} = -1 V, I _C = -10 mA
Collector cutoff current	I _{CEX}			0.05	μA	V _{CE} =-30 V, V _{BE} = -3 V
Base cutoff current	I _{BEX}			0.05	μA	V _{CE} =-30 V, V _{BE} = -3 V
Collector-Base Breakdown Voltage	BV _{CBO}	-40			V	I _C = -10μA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40			V	I _C = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -10μA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.4	V	I _C = -50 mA, I _B = -5 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			-0.95	V	I _C = -50 mA, I _B = -5 mA
Gain bandwidth product	f _T	250			MHz	I _C = -10 mA, V _{CE} = -20 V, f = 100 MHz
Common Base Output Capacitance	C _{ob}			4.5	PF	V _{CB} = -5 V, I _E =0, f = 1 MHz
Turn on Time	t _{on}			70	ns	V _{CC} = -3 V, V _{BE} =-0.5V, I _C = -10 mA, I _{B1} = -1mA
Turn off Time	t _{off}			300	ns	V _{CC} = -3 V, I _C = -10mA, I _{B1} =I _{B2} = -1mA

■ ■ h_{FE} Classification

Classification

h_{FE}

80 ~ 300